

BSIM4.x NQS MODEL FOR AC ANALYSIS

CR&D DEVICE MODELLING TEAM

NQS MODEL REQUIREMENTS FOR AC ANALYSIS

NQS model:

- ❑ **Should be the same as QS one at low frequencies.**

- ❑ **Should provide correct high frequency trends.**

Exemple: When used in common source mode, the MOS transistor transconductance magnitude, $|Y_m| = |Y_{21} - Y_{12}|$, should decrease when frequency increases.

AC NQS IMPLEMENTATION IN BSIM4.X

- ❑ A time constant, τ , is introduced, which is bias dependent.
- ❑ Considering the small signal [Y] matrix, each element, except Ybx ones, is multiplied by $\frac{1}{1 + j\tau\omega}$.

- ❑ For instance:

$$\left| \begin{array}{l} Y_{gd} = -j\omega C_{gd} \\ Y_{dg} = g_m - j\omega C_{dg} \end{array} \right. \text{ in QS model; } \left| \begin{array}{l} Y_{gd} = \frac{-j\omega C_{gd}}{1 + j\tau\omega} \\ Y_{dg} = \frac{g_m - j\omega C_{dg}}{1 + j\tau\omega} \end{array} \right. \text{ in NQS model.}$$

- ❑ This implementation in BSIM4 leads to the following expressions of Ym:

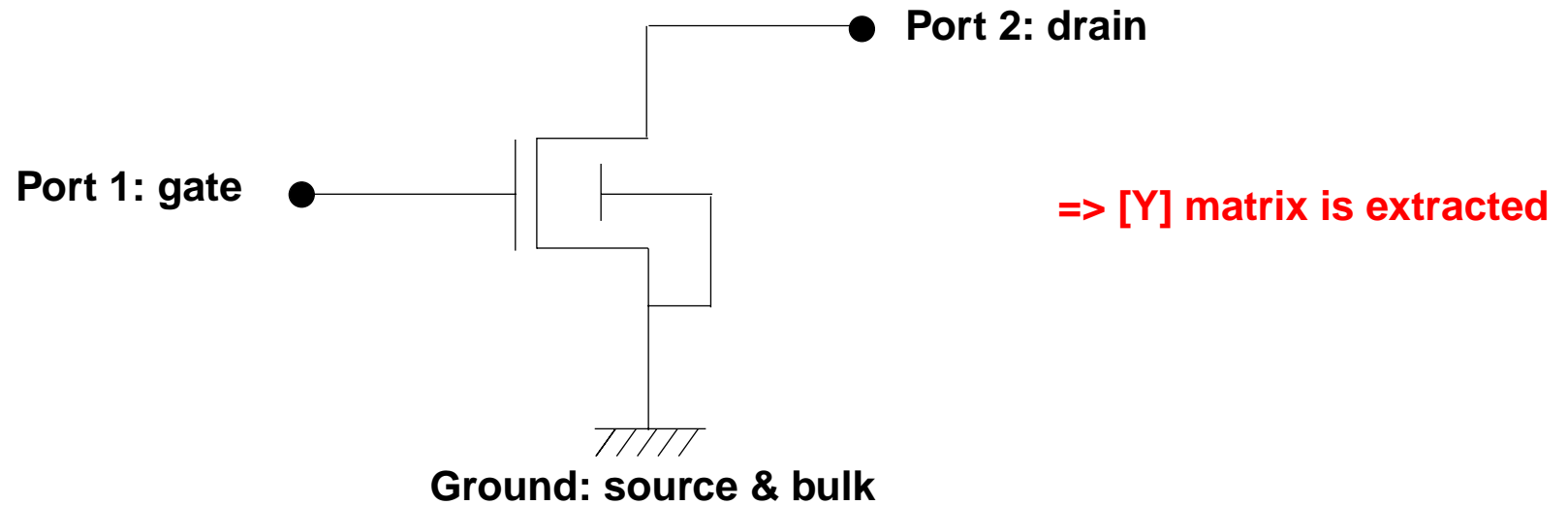
$$Y_m = g_m - j(C_{dg} - C_{gd})\omega \text{ in QS model; } Y_m = \frac{g_m - j(C_{dg} - C_{gd})\omega}{1 + j\tau\omega} \text{ in NQS model.}$$

- ❑ The term $-j(C_{dg} - C_{gd})\omega$ in the NQS expression should be removed since it corresponds to the low frequency approximation of $Y_m = \frac{g_m}{1 + j\tau\omega} \cong g_m - jg_m\tau\omega = g_m - j(C_{dg} - C_{gd})\omega$ [1].

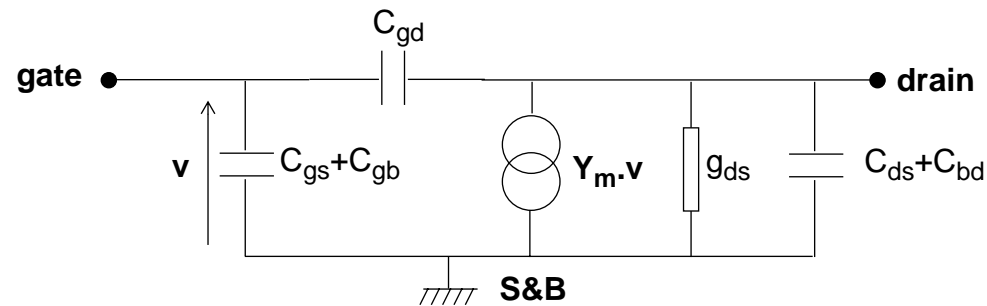
[1] Y. Tsididis, *Operation and Modeling of The MOS Transistor*, Second Edition, Chap. 9, "HF small-signal models".

COMPARISON WITH MEASUREMENTS: SETUP

- HF measurements were done on PMOS transistor biased common source:

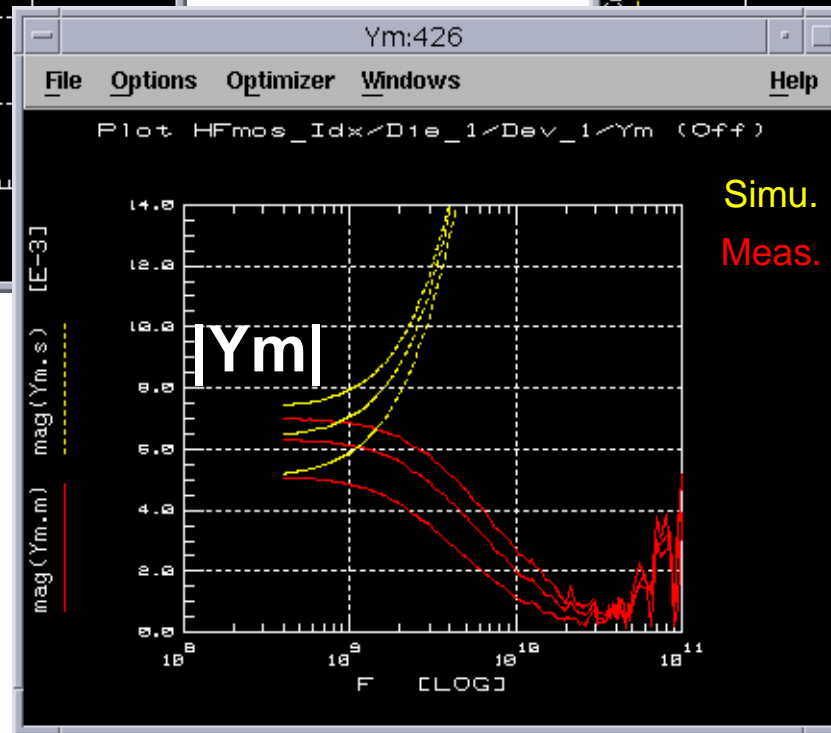
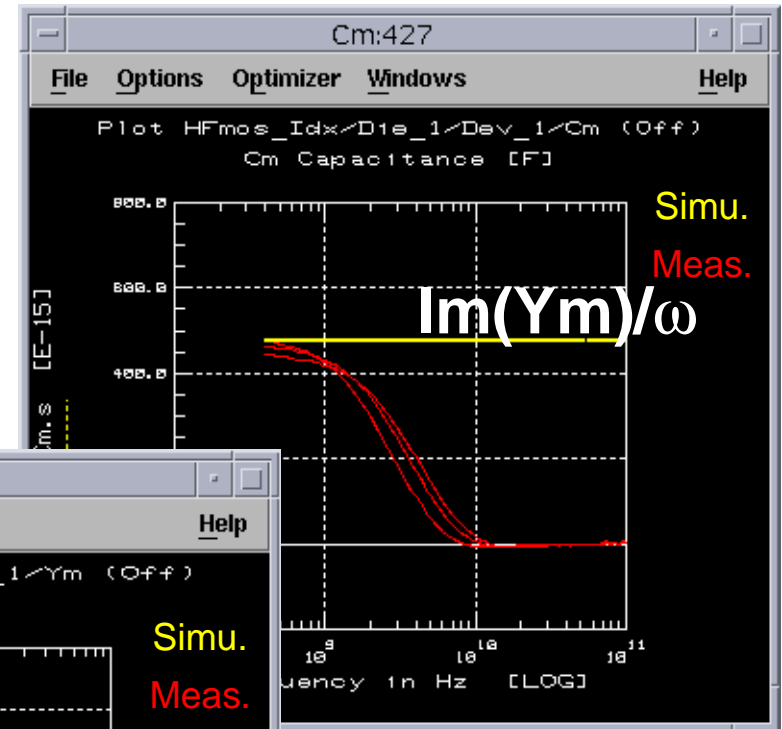
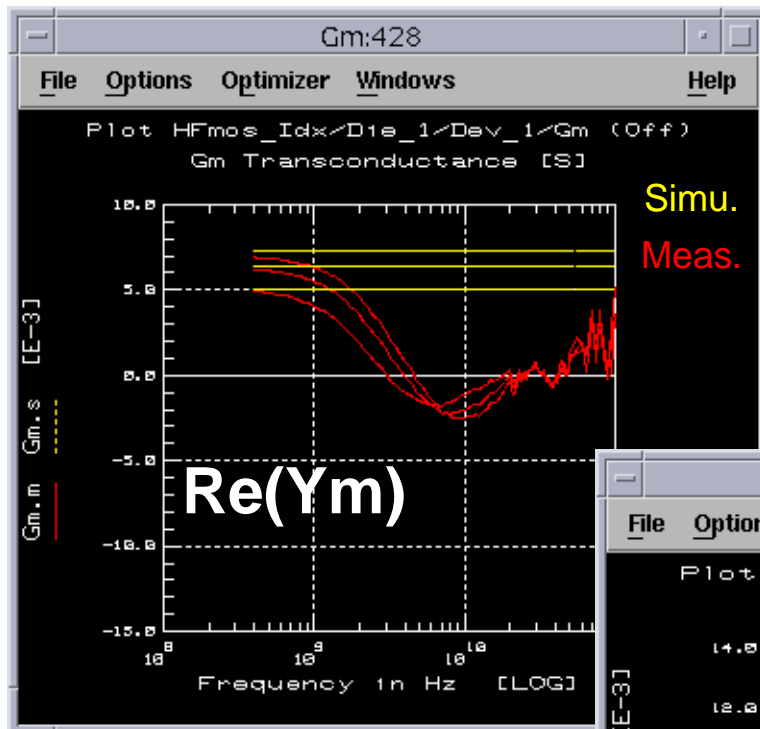


- Transconductance definition: $Y_m = (Y_{21} - Y_{12})$.



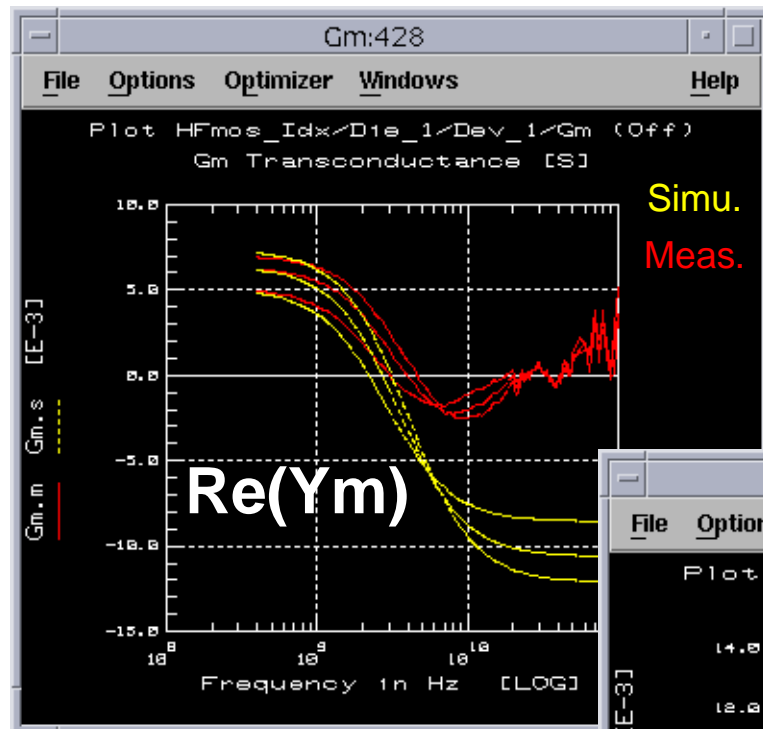
QS BSIM4.X MODEL VS. HF MEASUREMENTS

acnqsmod = 0



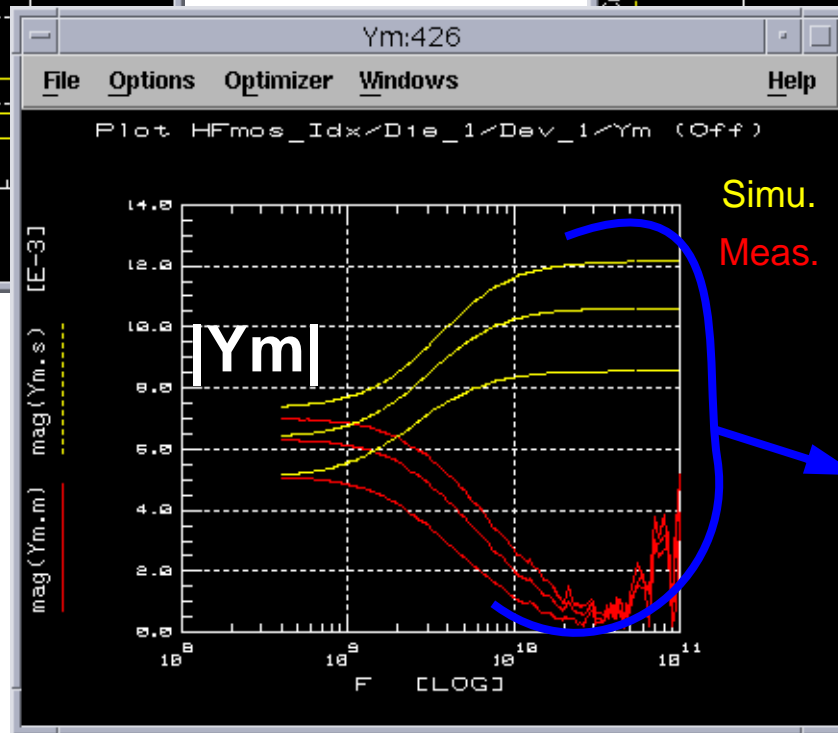
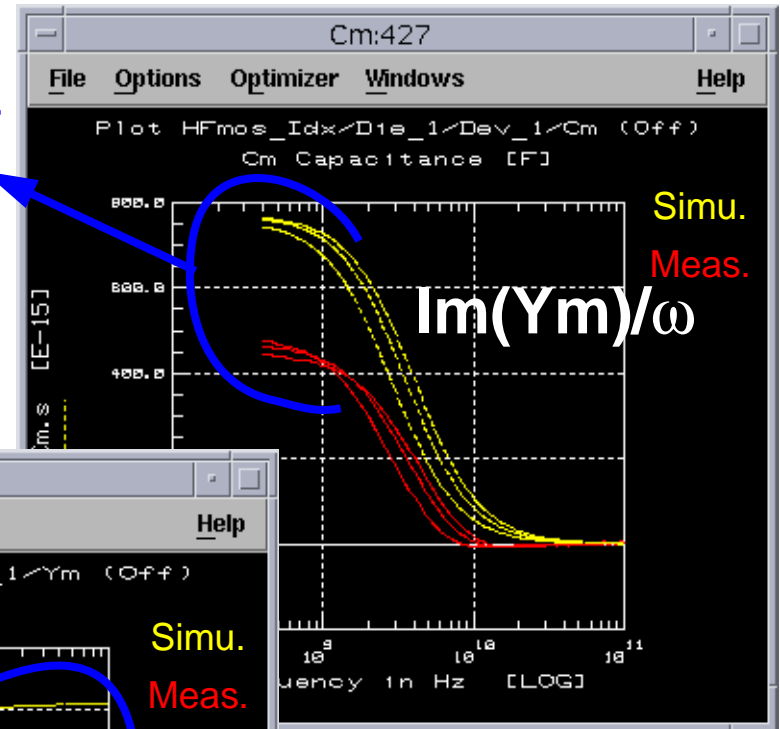
PMOS W = 120um, L = 1.2 um
Vds = -1.25V
Vgs = -0.75, -1.0 -1.25V

NQS BSIM4.X MODEL VS. HF MEASUREMENTS



acnqsmod = 1

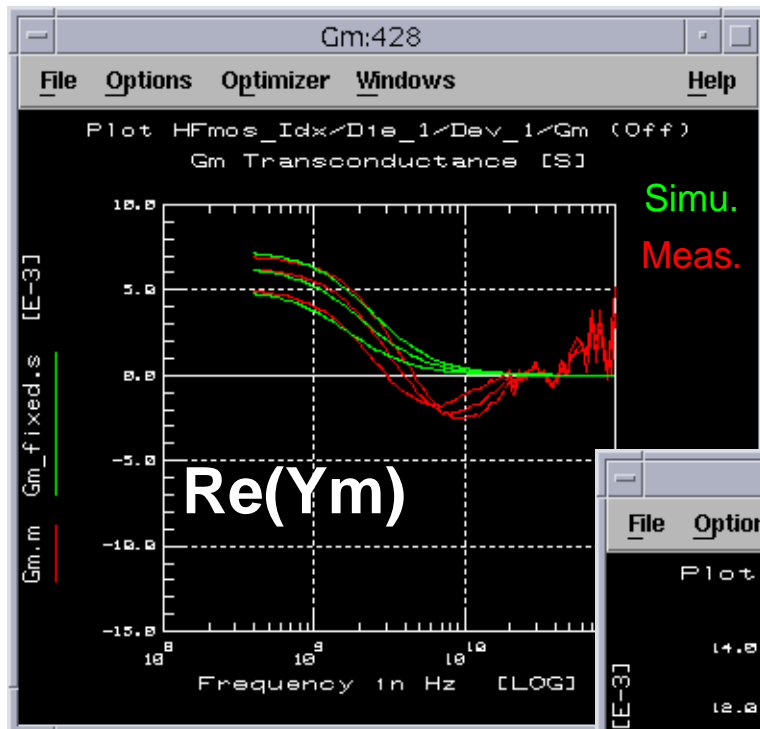
$\text{Im}(Y_m) / \omega$ at low F is not correct.



$|Y_m|$ still increases with F.

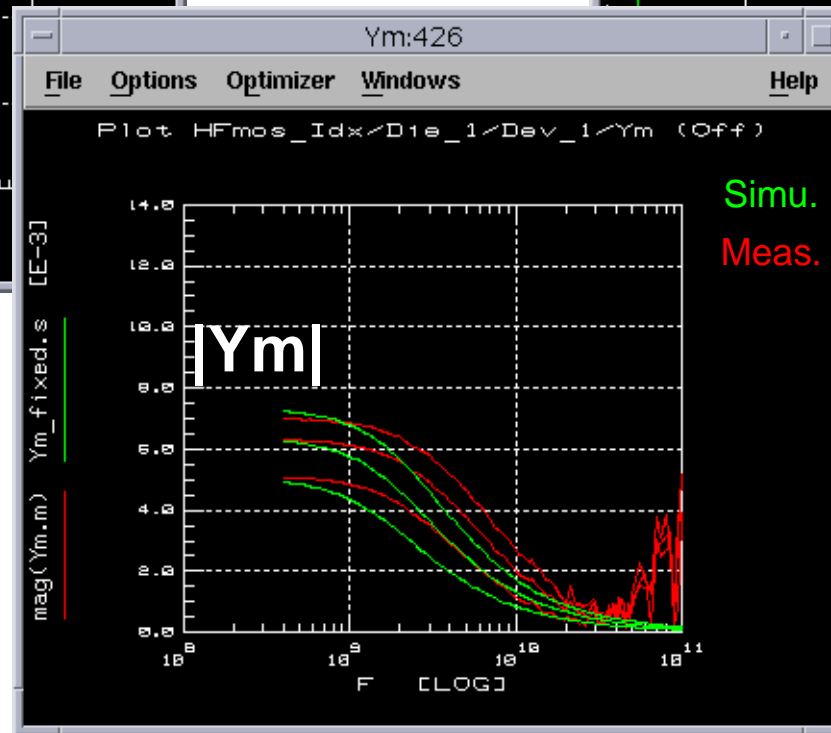
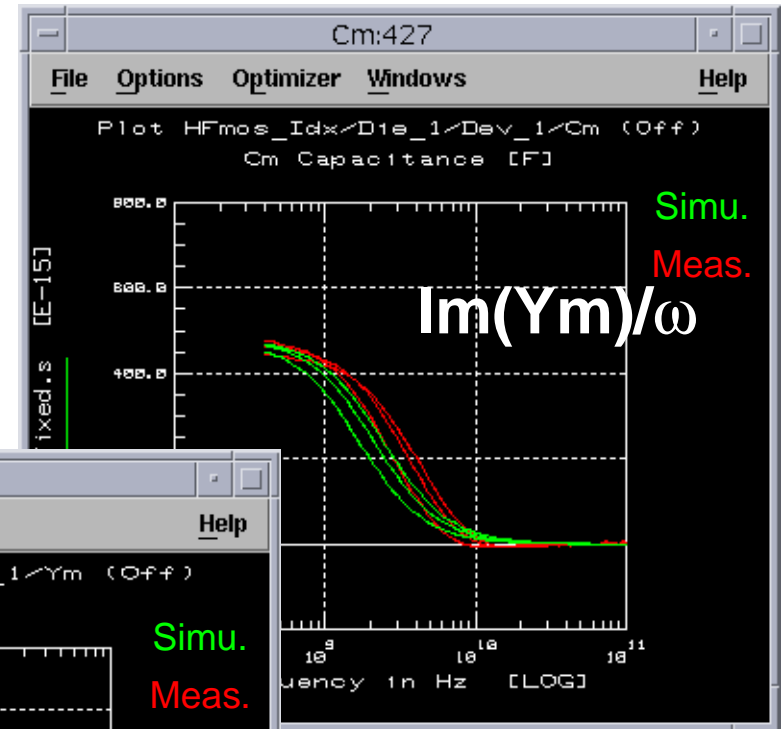
PMOS W = 120um, L = 1.2 um
 Vds = -1.25V
 Vgs = -0.75, -1.0 -1.25V

“FIXED” BSIM4.X MODEL VS. HF MEASUREMENTS



Ym with
 $-j(C_{dg} - C_{gd})\omega$
 term removed:

$$Y_m = \frac{g_m}{1 + j\tau\omega}$$



PMOS W = 120um, L = 1.2 um
 Vds = -1.25V
 Vgs = -0.75, -1.0 -1.25V

WHICH PART OF BSIM4.X C CODE SHOULD BE FIXED?

- Source code file is [b4acl.c](#) (same file for BSIM4.2.1, BSIM4.3.0, BSIM4.4.0):

```

if (here->BSIM4acnqsMod)
{
  T0 = omega * here->BSIM4taunet;
  T1 = T0 * T0;
  T2 = 1.0 / (1.0 + T1);
  T3 = T0 * T2;

  gmr = here->BSIM4gm * T2;
  gmbsr = here->BSIM4gmbs * T2;
  gdsr = here->BSIM4gds * T2;

  gmi = -here->BSIM4gm * T3;
  gmbsi = -here->BSIM4gmbs * T3;
  gdsi = -here->BSIM4gds * T3;

  Cddr = here->BSIM4cddb * T2;
  Cdgr = here->BSIM4cdgb * T2;
  Cdsr = here->BSIM4cdsb * T2;
  Cdbr = -(Cddr + Cdgr + Cdsr);

  /* WDLiu: Cxyi mulitplied by jomega below, and actually to be of conductance */
  Cddi = here->BSIM4cddb * T3 * omega;
  Cdgi = here->BSIM4cdgb * T3 * omega;
  Cdsi = here->BSIM4cdsb * T3 * omega;
  Cdbi = -(Cddi + Cdgi + Cdsi);

  Csdr = Csd * T2;
  Csgr = Csg * T2;
  Cssr = Css * T2;
  Csbr = -(Csdr + Csgr + Cssr);

  Csdi = Csd * T3 * omega;
  Csgi = Csg * T3 * omega;
  Cssi = Css * T3 * omega;

```

Terms to be set to 0 ?

CONCLUSION

- ❑ **A BSIM4.x NQS model implementation inconsistency has been shown for AC analysis.**
- ❑ **This leads to both incorrect high frequency trends and wrong imaginary parts at low frequencies.**
- ❑ **This has been illustrated for PMOS on Y_m transconductance frequency behavior.**
- ❑ **Similar observations were made on NMOS and other small-signal quantities than Y_m .**
- ❑ **A way to improve BSIM4.x NQS model codes capability is suggested.**
- ❑ **The whole BSIM4.x NQS model has to be checked, corrected and validated.**